

International IR Rectifier

RADIATION HARDENED POWER MOSFET SURFACE MOUNT (SMD-0.5)

IRHNJ57034
JANSR2N7480U3
60V, N-CHANNEL
REF: MIL-PRF-19500/703

R5 TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	ID	QPL Part Number
IRHNJ57034	100K Rads (Si)	0.030Ω	22A*	JANSR2N7480U3
IRHNJ53034	300K Rads (Si)	0.030Ω	22A*	JANSF2N7480U3
IRHNJ54034	600K Rads (Si)	0.030Ω	22A*	JANSG2N7480U3
IRHNJ58034	1000K Rads (Si)	0.038Ω	22A*	JANSH2N7480U3



International Rectifier's R5™ technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 (MeV/(mg/cm²)). The combination of low R_{DS(on)} and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Ultra low R_{DS(on)}
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
ID @ VGS = 12V, TC = 25°C	Continuous Drain Current	22*	A
ID @ VGS = 12V, TC = 100°C	Continuous Drain Current	21	
IDM	Pulsed Drain Current ①	88	
PD @ TC = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	100	mJ
IAR	Avalanche Current ①	22	A
EAR	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	10	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Pckg. Mounting Surface Temp.	300 (for 5s)	
	Weight	1.0 (Typical)	g

* Current is limited by package
For footnotes refer to the last page

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IRHNJ57034, JANSR2N7480U3

Pre-Irradiation

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.057	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DSON}	Static Drain-to-Source On-State Resistance	—	—	0.03	Ω	V _{GS} = 12V, I _D = 21A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	16	—	—	S (r _θ)	V _{DS} > =15V, I _{DS} = 21A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} =48V, V _{GS} =0V
		—	—	25		V _{DS} = 48V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	45	nC	V _{GS} = 12V, I _D = 22A V _{DS} = 30V
Q _{gs}	Gate-to-Source Charge	—	—	10		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	15		
t _{d(on)}	Turn-On Delay Time	—	—	25	ns	V _{DD} = 30V, I _D = 22A, V _{GS} = 12V, R _G = 7.5Ω
t _r	Rise Time	—	—	100		
t _{d(off)}	Turn-Off Delay Time	—	—	35		
t _f	Fall Time	—	—	30		
L _S + L _D	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C _{iss}	Input Capacitance	—	1152	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	535	—		
C _{rss}	Reverse Transfer Capacitance	—	42	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	22*	A	T _j = 25°C, I _S = 22A, V _{GS} = 0V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	88		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _j = 25°C, I _F = 22A, di/dt ≤ 100A/μs
t _{rr}	Reverse Recovery Time	—	—	125	ns	V _{DD} ≤ 25V ④
Q _{RR}	Reverse Recovery Charge	—	—	322	nC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

* Current is limited by package

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	1.67	°C/W	soldered to a 2" square copper-clad board
R _{thJ-PCB}	Junction-to-PC board	—	6.9	—		

Note: Corresponding Spice and Saber models are available on International Rectifier Web site

For footnotes refer to the last page

Radiation Characteristics

IRHNJ57034, JANSR2N7480U3

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ^{⑤⑥}

	Parameter	Up to 600K Rads(Si) ¹		1000K Rads (Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	60	—	60	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0	1.5	4.0		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	—	25	μA	V _{DS} =48V, V _{GS} =0V
R _{DS(on)}	Static Drain-to-Source ^④ On-State Resistance (TO-3)	—	0.034	—	0.043	Ω	V _{GS} = 12V, I _D = 21A
R _{DS(on)}	Static Drain-to-Source ^④ On-State Resistance (SMD-.5)	—	0.03	—	0.038	Ω	V _{GS} = 12V, I _D = 21A
V _{SD}	Diode Forward Voltage ^④	—	1.2	—	1.2	V	V _{GS} = 0V, I _S = 22A

1. Part numbers IRHNJ57034 (JANSR2N7480U3), IRHNJ53034 (JANSF2N7480U3) and IRHNJ54034 (JANSG2N7480U3)

2. Part number IRHNJ58034 (JANS2N7480U3)

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm ²)	Energy (MeV)	Range (μm)	V _{DS} (V)				
				@V _{GS} =0V	@V _{GS} =-5V	@V _{GS} =-10V	@V _{GS} =-15V	@V _{GS} =-20V
Br	37.3	285	36.8	60	60	60	60	40
Xe	63	300	29	46	46	35	25	15
Au	86.6	2068	106	35	35	27	20	14

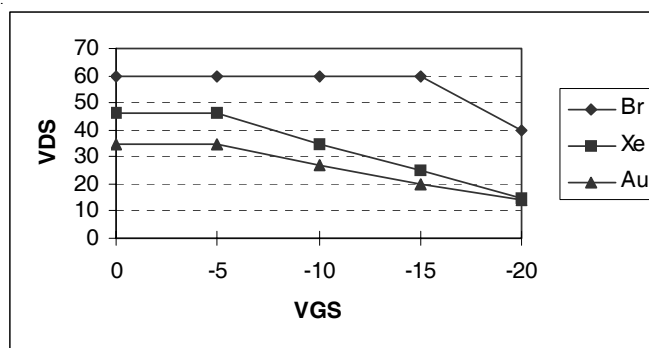


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

IRHNJ57034, JANSR2N7480U3

Pre-Irradiation

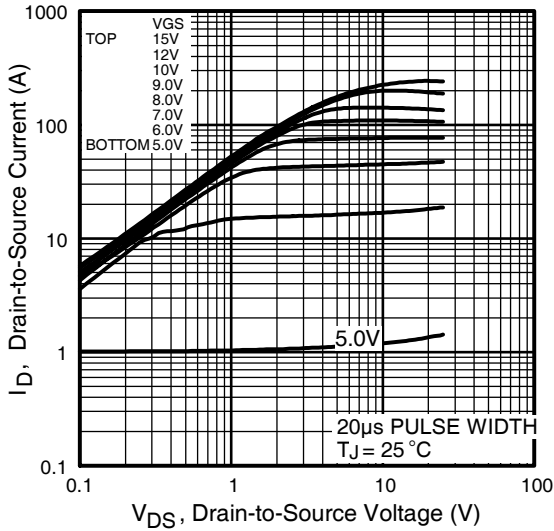


Fig 1. Typical Output Characteristics

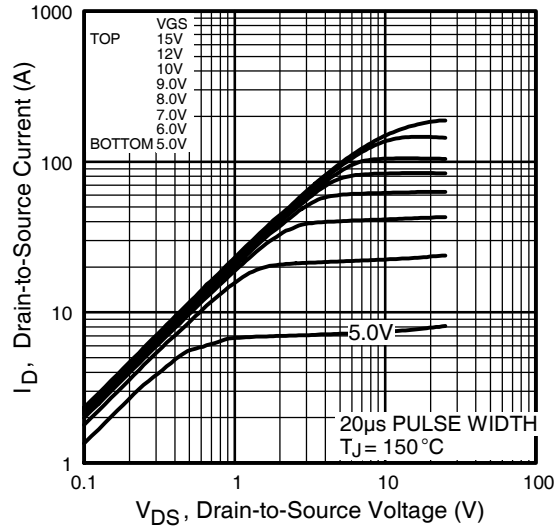


Fig 2. Typical Output Characteristics

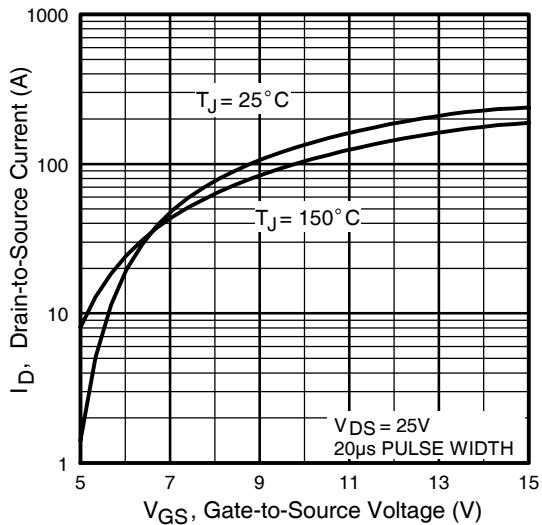


Fig 3. Typical Transfer Characteristics

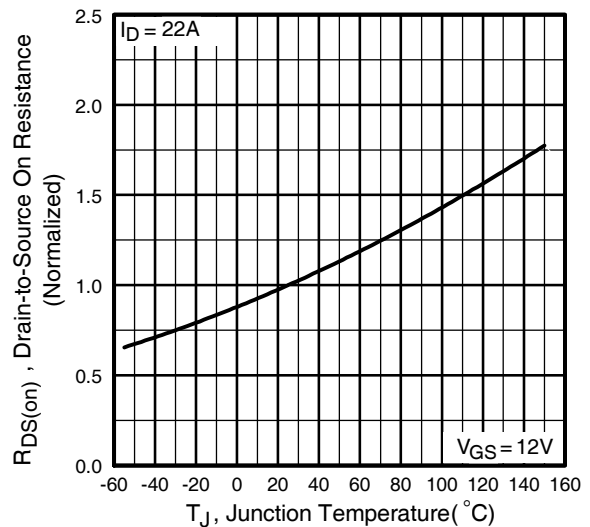


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

IRHNJ57034, JANSR2N7480U3

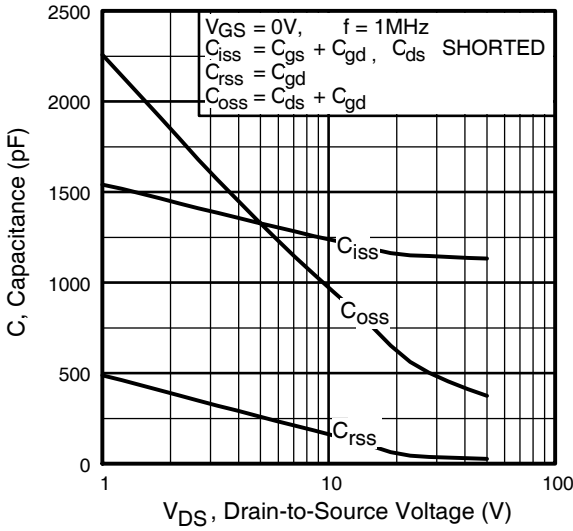


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

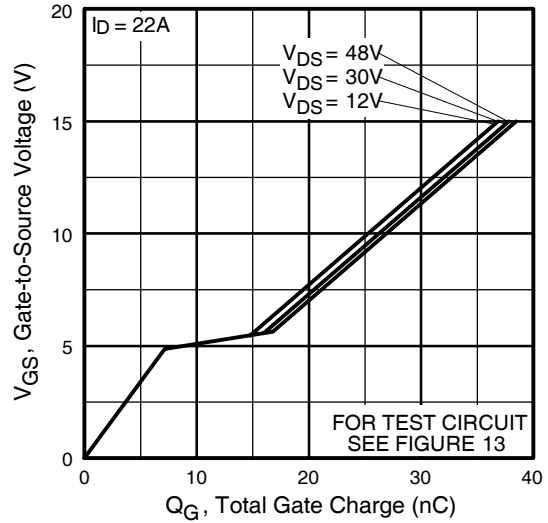


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

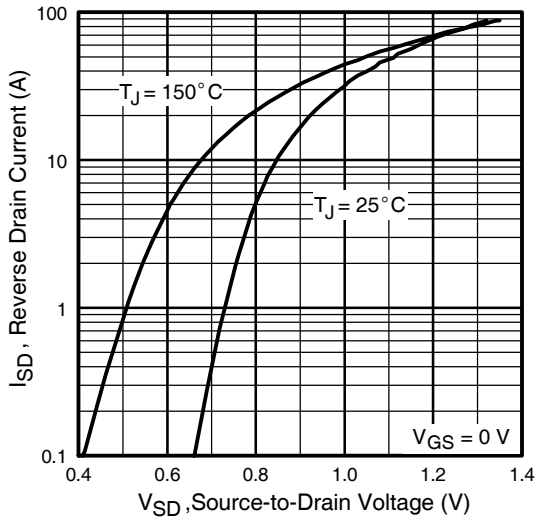


Fig 7. Typical Source-Drain Diode Forward Voltage

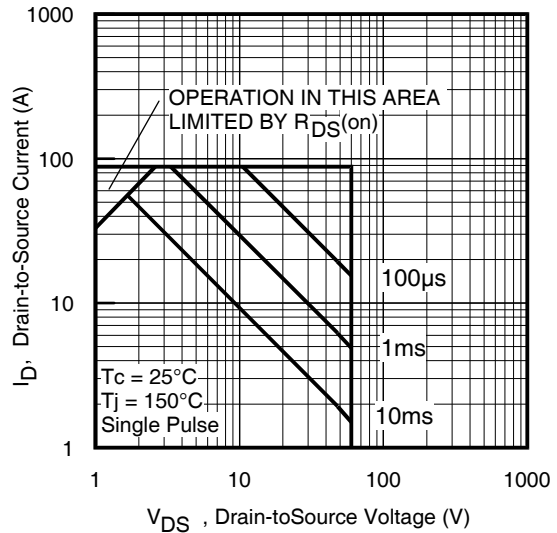


Fig 8. Maximum Safe Operating Area

IRHNJ57034, JANSR2N7480U3

Pre-Irradiation

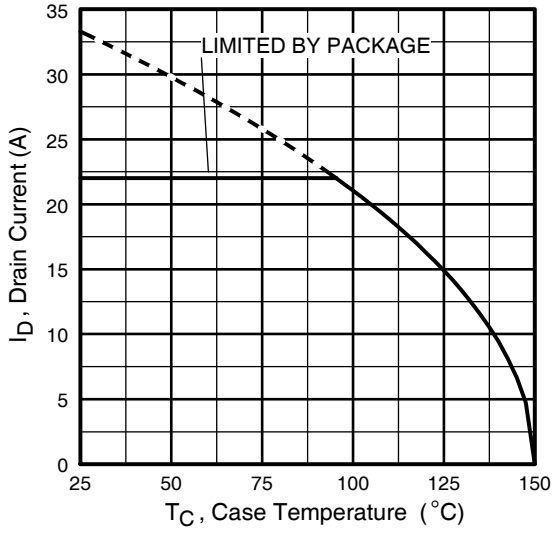


Fig 9. Maximum Drain Current Vs. Case Temperature

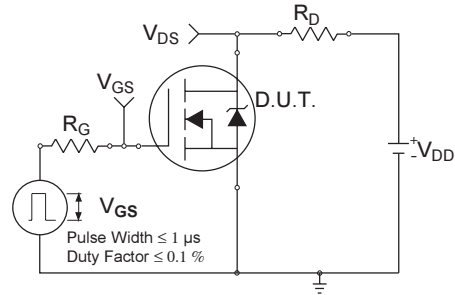


Fig 10a. Switching Time Test Circuit

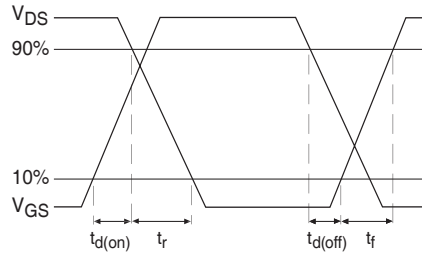


Fig 10b. Switching Time Waveforms

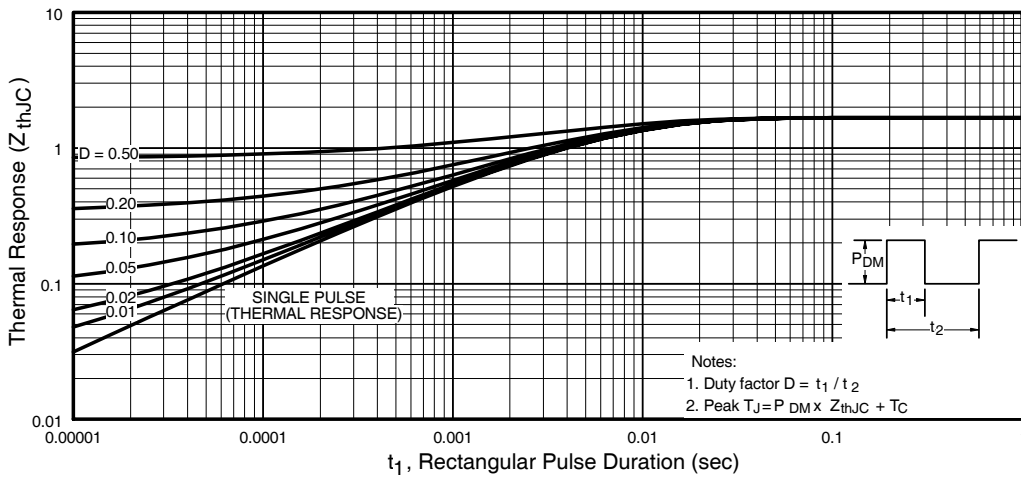


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Pre-Irradiation

IRHNJ57034, JANSR2N7480U3

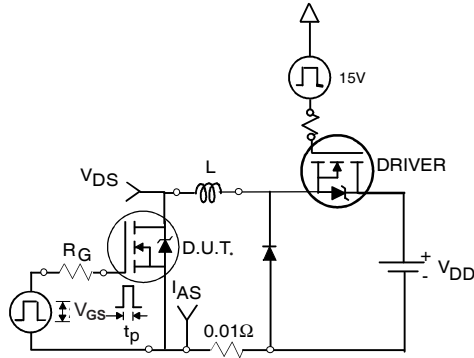


Fig 12a. Unclamped Inductive Test Circuit

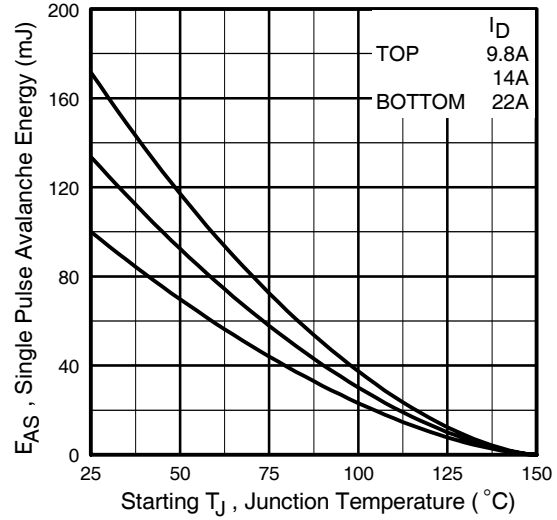


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

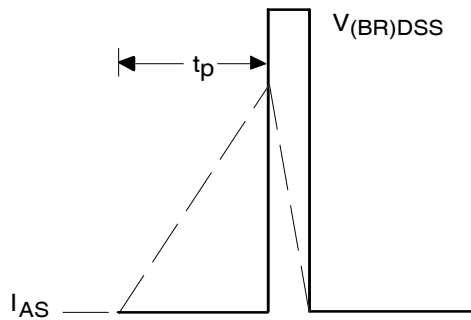


Fig 12b. Unclamped Inductive Waveforms

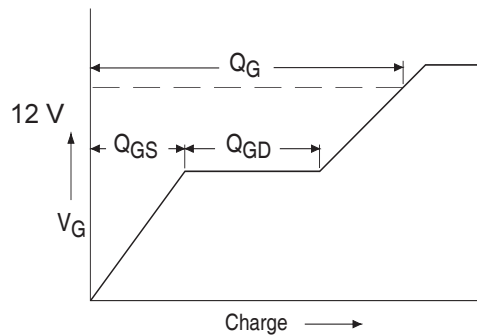


Fig 13a. Basic Gate Charge Waveform

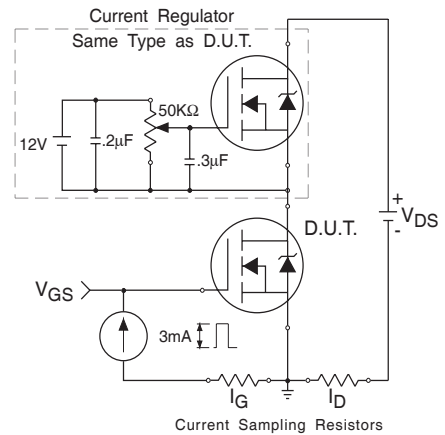


Fig 13b. Gate Charge Test Circuit

